



# 2SJ406

P-Channel Silicon MOS FET  
Very High-Speed Switching Applications

TENTATIVE

### Features and Applications

- Low ON-state resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

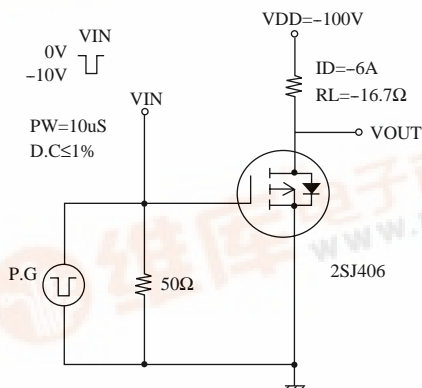
### Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	-200	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (D.C)	ID	-12	A
Drain Current (Pulse)	IDP	PW≤10μS, dutycycle≤1%	A
Allowable power Dissipation	PD	Tc=25°C	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

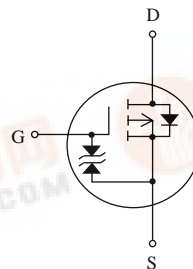
### Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-200			V
Gate to Source Breakdown Voltage	V(BR)GSS	ID=±100μA, VGS=0	±20			V
Zero Gate Voltage Drain Current	IDSS	VDS=-200V, VGS=0			-100	μA
Gate to Source Leakage Current	IGSS	VGS=±16V, VDS=0			±10	μA
Cutoff Voltage	VGS(OFF)	VDS=-10V, ID=-1mA	-1.5		-2.5	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-6A	6.3	10.5		S
Static Drain to Source on State Resistance	RDS(On)1	ID=-5A, VGS=-4V		170	230	mΩ
Input Capacitance	Ciss	VDS=-20V, f=1MHz		2400		pF
Output Capacitance	Coss	VDS=-20V, f=1MHz		540		pF
Reverse Transfer Capacitance	Crss	VDS=-20V, f=1MHz		260		pF
Turn-ON Delay Time	td(On)	See Specified Test Circuit .		40		ns
Rise Time	tr			120		ns
Turn-off Delay Time	td(Off)			720		ns
Fall Time	tf			310		ns
Diode Forward Voltage	VSD	IS=-1.0A, VGS=0	-1.0		-1.5	V

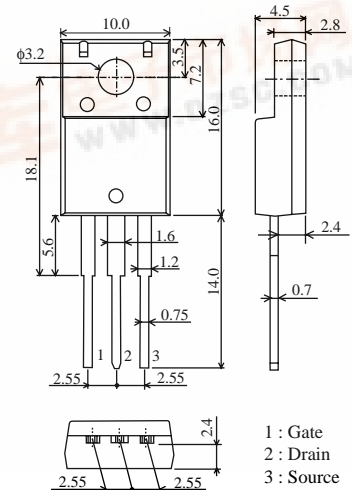
### Switching Time Test Circuit



### Electrical Connection



### Case Outline TO-220 (unit:mm)



Specifications and information herein are subject to change without notice.

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